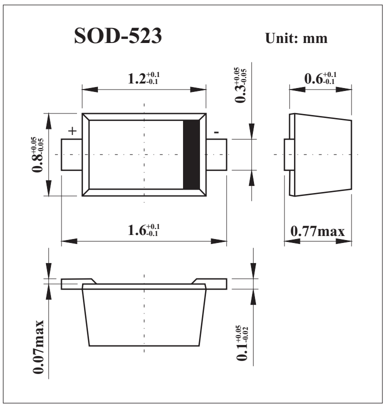
BAR64-02W



■ Features

- ● High voltage current controlled RF resistor for RF attenuator and switches
- ● Frequency range above 1 MHz
- ● Low resistance and short carrier lifetime
- ● Very low inductance
- ● For frequencies up to 3 GHz
- ● Extremely small plastic SMD package

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	200	V
Forward current	I_F	100	mA
Total power dissipation, $T_S \leqslant 125$℃	P_{tot}	250	mW
Junction temperature	T_j	150	℃
Operating temperature range	T_{op}	-55 to +150	℃
Storage temperature	T_{stg}	-55 to +150	℃
Junction - ambient (Note 1)	R_{thJA}	⩽ 220	K/W
Junction - soldering point	R_{thJS}	⩽ 140	

Note

1.Package mounted on alumina 15mm × 16.7mm × 0.7mm

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Breakdown voltage	V_R	$I_{(BR)}$ = 5 μA	200			V
Forward voltage	V_F	I_F = 50 mA			1.1	mV
Diode capacitance	C_T	V_R = 20 V, f = 1 MHz		0.23	0.35	pF
Case capacitance	C_C	f = 1 MHz		0.09		
Forward resistance	r_f	I_F = 1 mA, f = 100 MHz		12.5	20	Ω
		I_F = 10 mA, f = 100 MHz		2.1	3.8	
		I_F = 100 mA, f = 100 MHz		0.85	1.35	
Charge carrier life time	t_{rr}	I_F = 10 mA, I_R = 6 mA,I_R = 3 mA		1.55		μs
Series inductance	Ls			0.6		nH

■ Marking

Marking	M